

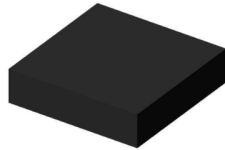
Product Summary

V_{RRM} (V)	I_o (A)	$V_{F(MAX)}$ (V) @ +25°C	$I_{R(MAX)}$ (mA) @ +25°C
45	4	0.52	0.1

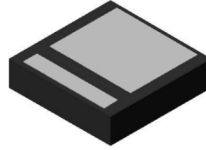
Description and Applications

The SBRT4U45LP provides very low V_F and excellent reverse leakage stability at high temperatures. It is ideal for use as bypass diode and rectifier, freewheel diode or blocking diode in applications such as:

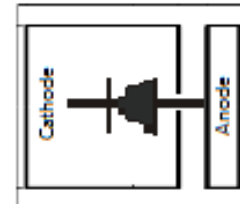
- Solar Panels
- Blocking Diode
- Bypass Diode
- Boost Diode
- Recirculating Diode



Top View



Bottom View



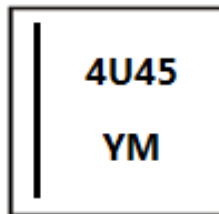
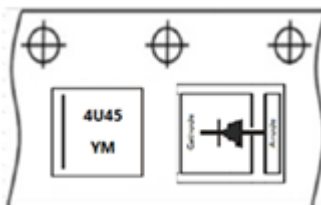
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
SBRT4U45LP-7	U-DFN2020-2 (Type B)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



4U45 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: B = 2014)
 M = Month (ex: 6 = June)
 Bar = Cathode

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022
Code	B	C	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitance load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V _R RM	45	V
Working Peak Reverse Voltage	V _R WM		
DC Blocking Voltage	V _R M		
Average Rectified Output Current	I _O	4	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	45	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Typical Thermal Resistance Junction to Case (Note 5)	R _θ JC	5	°C/W
Typical Thermal Resistance Junction to Ambient (Note 5)	R _θ JA	65	°C/W
Operating Temperature Range V _R ≤ 80% V _R RM V _R ≤ 50% V _R RM DC Forward Mode (Note 7)	T _J	-55 to +150 ≤+175 ≤+200	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage Drop (Note 6)	V _F	—	—	0.52	V	I _F = 4A, T _J = +25°C
Leakage Current (Note 6)	I _R	—	—	100	μA	V _R = 45V, T _J = +25°C
		—	4.7	—	mA	V _R = 45V, T _J = +125°C

Notes:
 5. Device mounted on FR-4 PCB pad layout 1-inch 2oz copper.
 6. Short duration pulse test used to minimize self-heating effect.
 7. Max junction temperature guaranteed for two hours.

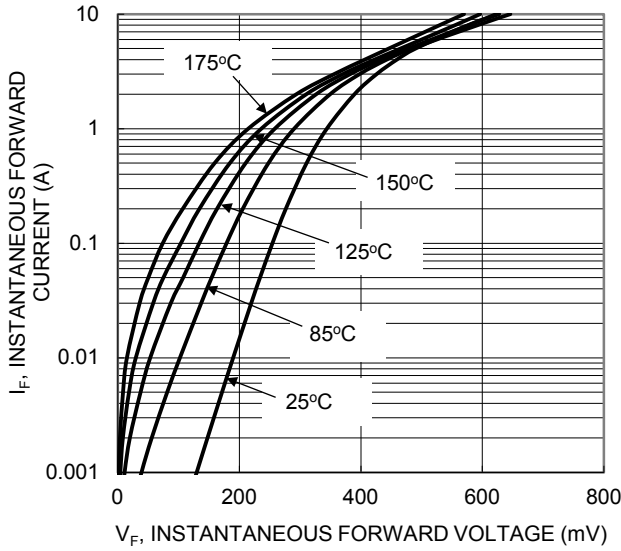


Figure 1 Typical Forward Characteristics

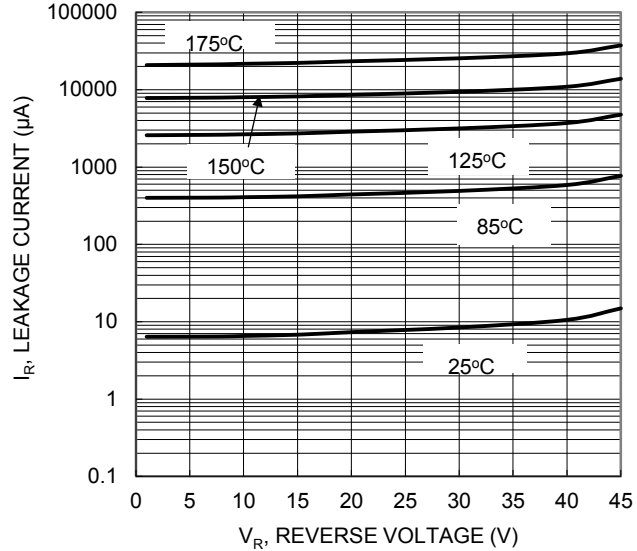


Figure 2 Typical Reverse Characteristics

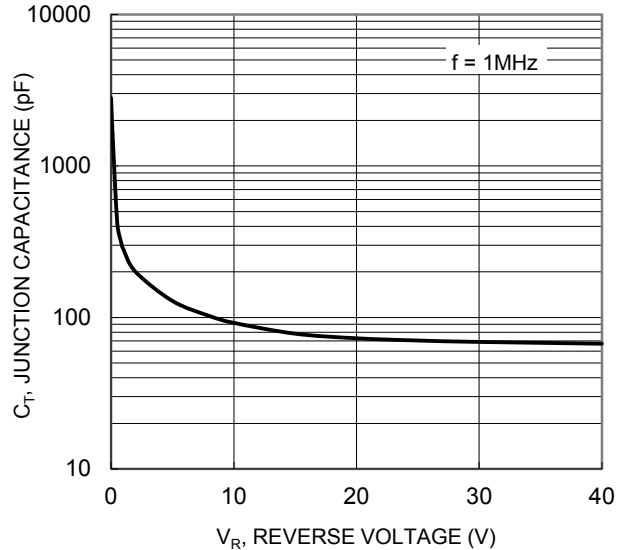


Figure 3 Typical Junction Capacitance

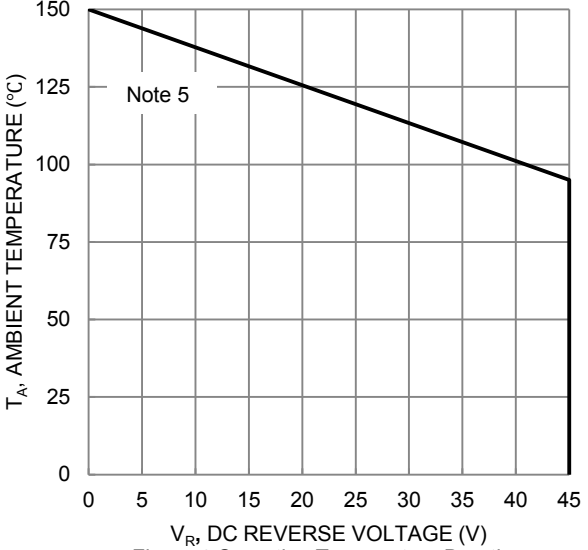


Figure 4 Operating Temperature Derating

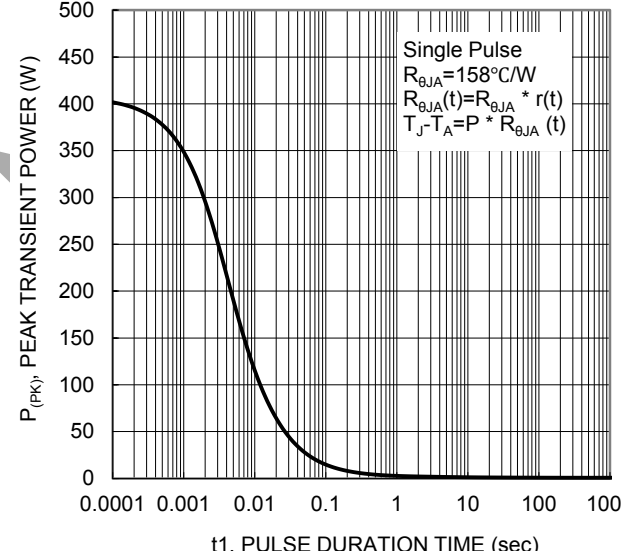


Figure 5 Single Pulse Maximum Power Dissipation

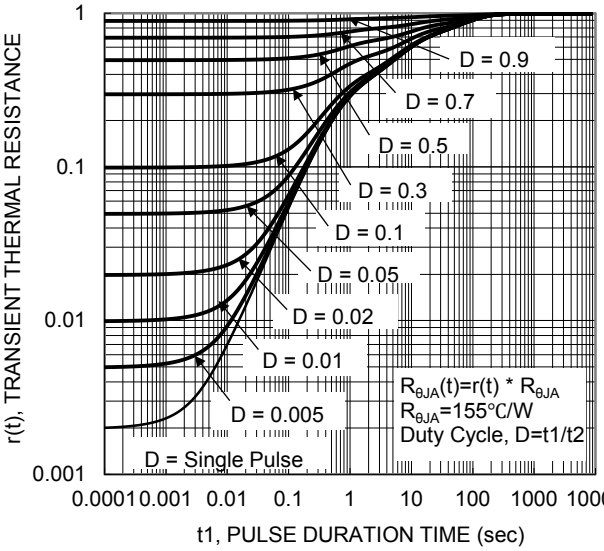
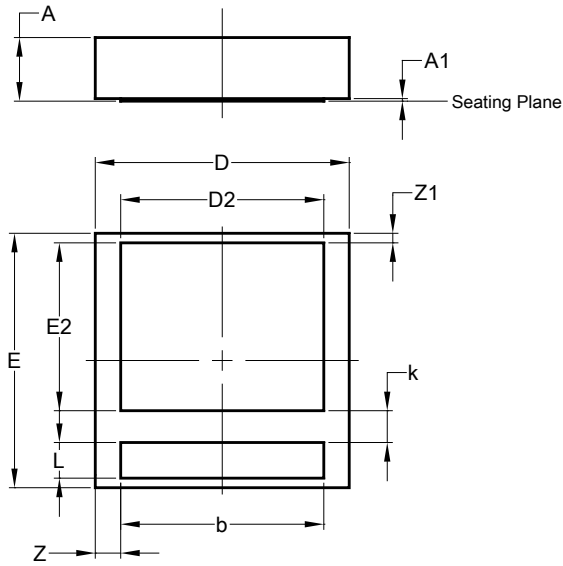


Figure 6 Transient Thermal Resistance

Package Outline Dimensions

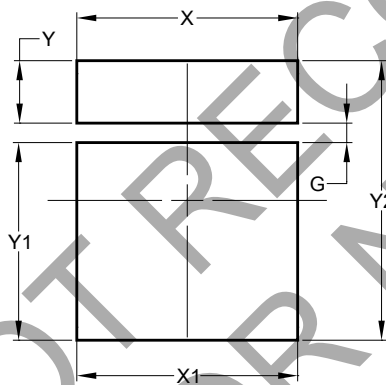
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN2020-2 (Type B)			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.02
b	1.55	1.65	1.60
D	1.95	2.05	2.00
D2	1.50	1.70	1.60
E	1.95	2.05	2.00
E2	1.22	1.42	1.32
k	0.25 BSC		
L	0.23	0.33	0.28
Z	0.20 BSC		
Z1	0.075 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
G	0.150
X	1.700
X1	1.700
Y	0.480
Y1	1.520
Y2	2.150

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